L Number	Hits	Search Text	DB	Time stamp
-	628447	DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 11:54
		capacitor\$1	US-PGPUB;	
		•	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	12833	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1)	USPAT;	2004/03/15 15:50
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	3878	(DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 11:55
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	34706	(bury or buried) near3 (layer\$1 or film\$1)	USPAT;	2004/03/15 11:56
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	753		USPAT;	2004/03/15 12:40
1		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	20040014329.URPN.	USPAT	2004/03/15 12:00
-	268974	source\$1 and drain\$1	USPAT;	2004/03/15 12:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	16200	(and an explain the first come (as between an explain come	IBM_TDB USPAT;	2004/03/15 12:42
-	16200	(remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same	US-PGPUB;	2004/03/13 12.42
		(hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	756023	(top or upper or second) near4 (plate\$1 or electrode\$1)	USPAT;	2004/03/15 12:43
	1,30023	(top of apper of second) field (plates) of electrodes)	US-PGPUB;	250 1100/10 12.40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	121	(((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 12:44
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))) and	ЕРО; ЛРО;	
		(source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same	DERWENT;	
		(substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or	IBM_TDB	
		groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1))	_	
-	47376	storag\$4 near4 (plate\$1 or electrode\$1)	USPAT;	2004/03/15 12:45
]			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
		·	IBM_TDB	

		((DD +) (f) (1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	HODAT	2004/02/15 12 40
-	53	((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	USPAT;	2004/03/15 12:49
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or	US-PGPUB;	
		MOSFET\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4)	ЕРО; ЛРО;	
		same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or	DERWENT;	
		via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4	IBM_TDB	
		(plate\$1 or electrode\$1)) and ((((DRAM\$1 or (dynamic adj random adj		
		access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or		
	1	transistor\$1 or MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or		
	ļ.	film\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same		
		drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or		
		open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or		
		electrode\$1))) and (storag\$4 near4 (plate\$1 or electrode\$1))		
-	758663	(lower or bottom or first) near4 (electrode\$1 or plate\$1)	USPAT;	2004/03/15 15:42
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM TDB	
_	968	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 15:45
		(438/248) or (438/249)).CCLS.	US-PGPUB	200 1100110 10110
_	741	((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or	USPAT;	2004/03/15 15:46
-	, , ,	(438/391) or (438/392)).CCLS.	US-PGPUB	200 1/03/13 13:10
_	1293	(((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 15:47
	1273	((438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or	US-PGPUB	2004/03/13 13.47
1		(438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)	05-1 G1 0D	
	1892	((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or	USPAT;	2004/03/15 15:50
-	1072	(438/242) or (438/268) or (438/270) or (438/271)).CCLS.	US-PGPUB	2004/03/13 13.30
	46651	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)	USPAT;	2004/03/15 15:50
-	40051	vertically rically (1910) of transfision of the 1910 of characters;	US-PGPUB;	2004/03/13 13.50
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
	124	(vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3))	USPAT;	2004/03/15 16:08
-	124		-	2004/03/13 10.08
		and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	US-PGPUB;	
		capacitor\$1) and ((bury or buried) near3 (layer\$1 or film\$1)) and	ЕРО; ЛРО;	
		(source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same	DERWENT;	
	ļ	(substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or	IBM_TDB	
		groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1))		
1		and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower or bottom or		
		first) near4 (electrode\$1 or plate\$1)))	110D + M	2004/02/15 16 00
-	131	(((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or	USPAT;	2004/03/15 16:09
		(438/242) or (438/268) or (438/270) or (438/271)).CCLS.) and	US-PGPUB;	
		(DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	ЕРО; ЈРО;	
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1	DERWENT;	
		or channel\$3)) and ((top or upper or second) near4 (plate\$1 or	IBM_TDB	
		electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower		
		or bottom or first) near4 (electrode\$1 or plate\$1)))		
-	129	((((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or	USPAT;	2004/03/15 16:09
		(438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or	US-PGPUB;	
		(438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.))	ЕРО; ЈРО;	
		and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or	DERWENT;	
		capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1	IBM_TDB	
		or channel\$3)) and ((top or upper or second) near4 (plate\$1 or		
		electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower		
	1	or bottom or first) near4 (electrode\$1 or plate\$1)))		I